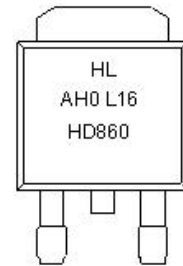


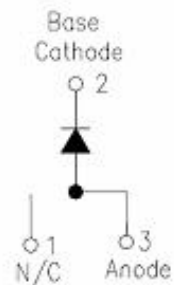
HD860 ULTRAFAST RECTIFIER

Features:

- Ultra-Fast Switching
- High Current Capability
- Low Reverse Leakage Current
- High Surge Current Capability
- Plastic Material has UL Flammability Classification 94V-0
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



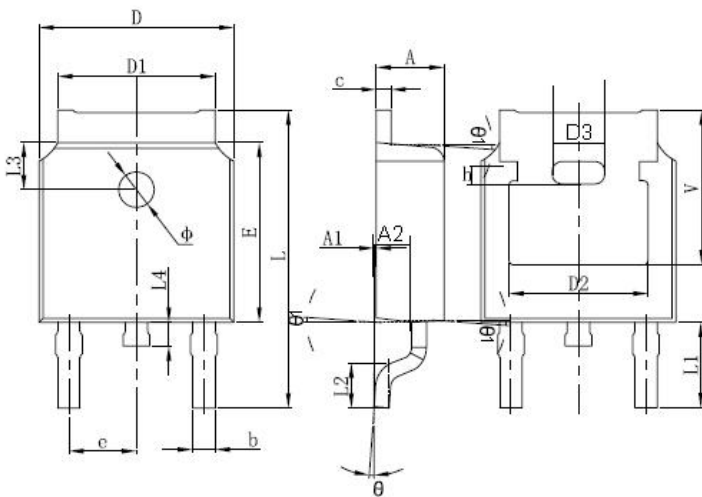
HD860



Mechanical Data:

- Case: Molded Plastic
- Terminals: Plated Leads, Solderable per MIL-STD-202, Method 208
- Weight: 0.39 grams (approx.)
- Marking: Type Number
- Mounting Position: Any

Mechanical Dimensions: In mm /Inches



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.380	0.087	0.094
A10.000	0.000	0.100	0.000	0.004
b	0.710	0.810	0.028	0.032
c	0.460	0.560	0.018	0.022
D	6.500	6.700	0.256	0.264
D1	5.130	5.460	0.202	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
A2	0.910	1.110	0.036	0.044
V	5.350 REF.		0.211 REF.	
D3	1.778 REF.		0.070 REF.	
h	0.762 REF.		0.030 REF.	
θ1	7°		7°	

DPAK

MARKING, MOLDING RESIN

Marking for HD860, 1st row HL, 2nd row AH0 LXX, 3rd row HD860
Where XX is Determined by customer

- China - Germany - Korea - Singapore - United States •
- <http://www.smc-diodes.com> - sales@smc-diodes.com •

Ordering Information:

Device	Package	Shipping
HD860	DPAK (Pb-Free)	2500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings and Electrical Characteristics @ $T_A=25^{\circ}\text{C}$ unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

Characteristic	Symbol	HD860	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	600	V
RMS Reverse Voltage	$V_{R(RMS)}$	420	V
Average Rectified Output Current @ $T_A = 100^{\circ}\text{C}$	I_o	8.0	A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	110	A
Forward Voltage (per element) @ $I_F = 8.0\text{A}$, $T_J = 25^{\circ}\text{C}$	V_{FM}	1.7	V
Peak Reverse Current @ $T_A = 25^{\circ}\text{C}$ At Rated DC Blocking Voltage @ $T_A = 100^{\circ}\text{C}$	I_{RM}	5.0 50	μA
Maximum Reverse Recovery Time (Note 1)	T_{rr}	50	ns
Max. Voltage Rate of Change	dv/dt	10,000	V/ μs
Typical Thermal Resistance Junction to Ambient (Note 2)	$R_{\theta JA}$	25	K/W
Storage Temperature Range	T_{STG} , T_J	-55 to +150	$^{\circ}\text{C}$
Case Style	DPAK		

- Note:**
- Reverse Recovery Test Conditions: $I_F=0.5\text{A}$, $I_R=1.0\text{A}$, $IRR=0.25\text{A}$
 - Mount on Cu-Pad Size 16mm×16mm on P.C.B.

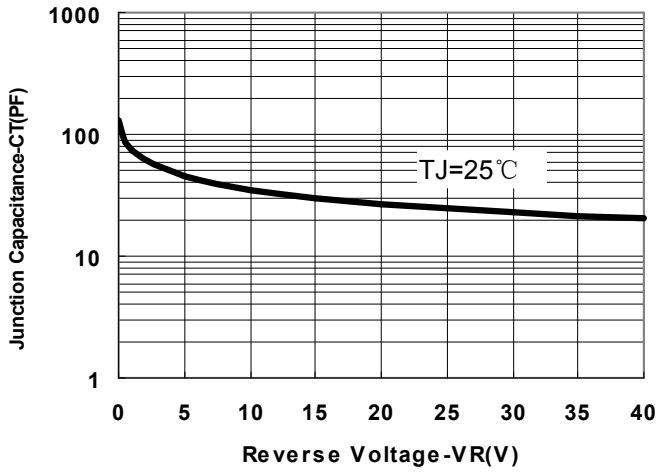


Fig.1-Typical Junction Capacitance

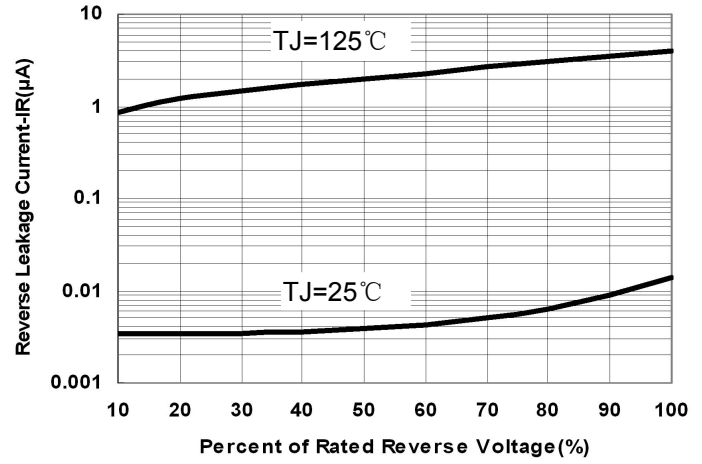


Fig.2-Typical Reverse Characteristics

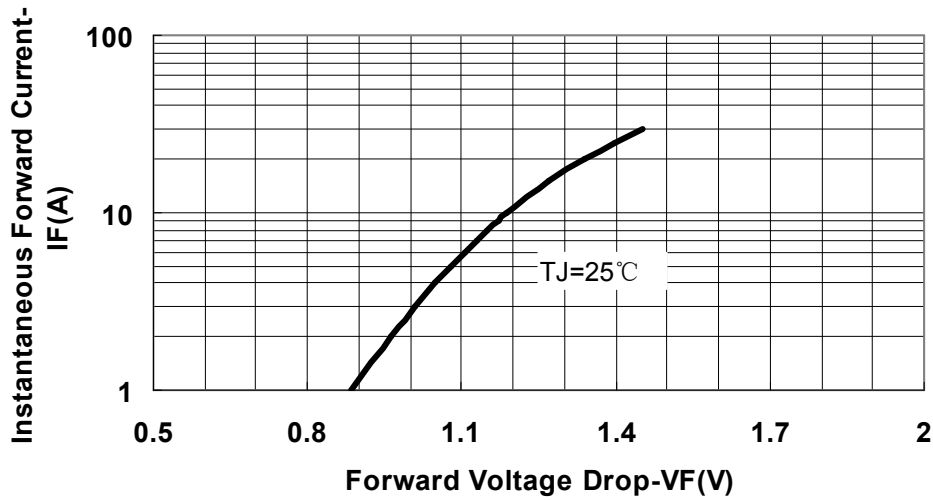


Fig.3-Typical Forward Voltage Drop Characteristics

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